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Trends in the Development of Bioresorbable Scaffolds

I.D. Kirilenko[1], M.S. Ruzhevich[1], N.L. Bazhenov[2], M.V. Tomkovich[2], V.V. Romanov[2], K.D. Moiseev[2], K.D. Mynbaev[1,2]

[1] Institute of Advanced Data Transfer, ITMO University, 49 Kronverkskiy, Saint-Petersburg 197101
[2] Ioffe Institute, 26 Polytechnicheskaya, Saint-Petersburg 194021

Received: November 22, 2024 Corresponding author: I.D. Kirilenko

Abstract. This article presents the results of a study of current-voltage (*I–V*) characteristics of InAsSb/InAsSbP heterostructures with an InSb content in the InAsSb active region 0.06 and 0.09. Using these results, the results of electroluminescence studies, and the data of energy-dispersive X-ray spectroscopy obtained for InAsSbP films grown on InAs(Sb), it is shown that the peculiarities of formation of the InAsSb/InAsSbP heterointerface via the method of metalorganic vapor phase epitaxy can lead to the development of a type II heterojunction. At temperatures $T \leq 170$ K, this is manifested in specific values of both the energy of electroluminescence spectrum maximum and the *I–V* cutoff value.

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